

HYBRID STRUCTURE FOR A SURFACE ACOUSTIC WAVE DEVICE

FIELD OF THE INVENTION

The present invention relates to the field of surface acoustic wave devices. It particularly relates to a hybrid structure suitable for manufacturing surface acoustic wave devices.

TECHNOLOGICAL BACKGROUND OF THE INVENTION

Acoustic resonator structures such as surface acoustic wave (SAW) devices use one or several interdigital transducers produced on a piezoelectric substrate in order to convert electrical signals into acoustic waves and vice versa. SAW devices or resonators of this kind are often used in filtering applications. Radiofrequency (RF) SAW technology provides excellent performances including a high level of insulation and low insertion losses. This is why it is used for RF duplexers in wireless communication applications. Nevertheless, in order to be more competitive versus RF duplexers based on bulk acoustic wave (BAW) technology, the performance of the RF SAW devices needs to be improved and it is required in particular that the frequency response be temperature-stable.

The temperature dependence of the operating frequency of SAW devices, or the temperature coefficient of frequency (TCF), depends on the one hand on variations in the spacing between the interdigital electrodes of the transducers, which are generally due

to the relatively high coefficients of thermal expansion (CTE) of the piezoelectric substrates used; on the other hand, the TCF depends on the thermal velocity coefficient, since expansion or contraction of the piezoelectric substrate is accompanied by an increase or decrease in the surface acoustic wave velocity. In order to minimise the temperature coefficient of frequency (TCF), an objective is therefore to minimise the expansion/contraction of the piezoelectric substrate, particularly in the surface area in which the acoustic waves will propagate.

The article by K.Hashimoto, M.Kadota et al, "Recent development of temperature compensated SAW devices", IEEE Ultrason. Symp. 2011, pages 79 à 86, 2011, provides an overview of the approaches commonly used to overcome the temperature dependence problem of the frequency response of SAW devices.

The first approach involves covering the surface of the piezoelectric substrate comprising the metallic structure of the transducers with a layer of silicon oxide (SiO_2). The very low CTE of SiO_2 limits the temperature expansion/contraction of the piezoelectric substrate. Although it improves temperature performance, this approach has limitations: on the one hand, the temperature constraints for applying this oxide layer (given the presence of metals) only provide access to relatively poor quality materials with limited acoustic performance; on the other hand, with this approach, the final thickness of the piezoelectric substrate must be greater than 200 microns to guarantee

the mechanical strength of the structure, which restricts the final packaging possibilities of the device.

The second approach involves using a hybrid
5 substrate, composed for instance of a layer of
piezoelectric material applied to a silicon substrate.
In this case also, the low CTE of silicon limits the
temperature expansion/contraction of the piezoelectric
layer. In the case of a piezoelectric layer of Lithium
10 Tantalate (LiTaO_3), the article mentioned above
indicates that a ratio of 10 between the LiTaO_3
thickness and the thickness of the silicon substrate
suitably improves the temperature coefficient of
frequency (TCF). One of the drawbacks of this approach
15 lies in the presence of parasitic acoustic waves (known
as "spurious acoustic modes" in the article
"Characterization of bonded wafer for RF filters with
reduced TCF", B. P. Abbott et al, Proc 2005 IEEE
International Ultrasonics Symposium, Sept 19-21, 2005,
20 pp.926-929) which negatively impact the frequency
characteristics of the resonator produced on the hybrid
substrate. These spurious resonances are particularly
related to spurious reflections of the main acoustic
wave (propagating mainly in a superficial area of the
25 LiTaO_3 layer) on the underlying interfaces, including in
particular the interface between the LiTaO_3 and silicon.
A solution in order to reduce these spurious resonances
involves increasing the thickness of the layer of
 LiTaO_3 ; since this implies an increase in the thickness
30 of the Si substrate in order to maintain the
improvements in the TCF, the total thickness of the

hybrid substrate is no longer compatible with the requirements for reducing the thickness of the final components, notably to address the cell phone market. Another solution, proposed by K.Hashimoto et al. (Article previously mentioned) involves roughening the lower surface of the layer of LiTaO_3 (at the bonding interface with the substrate) so as to limit the reflections of the acoustic wave on said surface.

AIM OF THE INVENTION

An aim of the present invention is to provide an alternative solution to the state-of-the-art solutions. An aim of the invention particularly involves providing a hybrid structure allowing reduction and/or elimination of said spurious acoustic waves.

BRIEF DESCRIPTION OF THE INVENTION

The present invention relates to a hybrid structure for a surface acoustic wave device comprising a useful layer of piezoelectric material joined to a carrier substrate having a thermal expansion coefficient lower than that of the useful layer, wherein the hybrid structure is remarkable in that it comprises an intermediate layer located between the useful layer and the carrier substrate, the intermediate layer being a structured layer formed of at least two different materials having a plurality of periodic motifs in the plane of said intermediate layer.

The lateral dimensions, the periodicity of the motifs in the plane of the intermediate layer and the thickness of the intermediate layer are defined according to the frequency of the acoustic wave characteristic of the SAW device in order to transmit or diffuse the acoustic waves normally reflected on the interfaces of the hybrid structure. The presence of the intermediate layer in the hybrid structure therefore drastically reduces the parasitic reflections of the acoustic wave that negatively impact the frequency characteristics of the SAW device.

According to advantageous characteristics of the invention, taken either separately or in combination:

- the periodicity of the motifs is selected according to the frequency of the surface acoustic waves of the device;
- the carrier substrate comprises a material selected from among silicon, glass, silica, sapphire, alumina and aluminium nitride;
- the useful layer comprises a piezoelectric material selected from among lithium tantalate (LiTaO_3), lithium niobate (LiNbO_3), quartz and zinc oxide (ZnO);
- the mean acoustic impedance of the intermediate layer is substantially equal to the square root of the product of the acoustic impedances of the useful layer and of the carrier substrate;

- the thickness of the intermediate layer is greater than the wavelength of the surface acoustic waves of the device;

- at least one lateral dimension of the motifs is smaller than the wavelength of the surface acoustic waves of the device;

- the periodic motifs comprise an alternation of a first motif composed of the material of the useful layer and of a second motif composed of a material of the same type as that of the carrier substrate;

- the second motif is composed of polycrystalline silicon and the carrier substrate is made of silicon;

- the thickness of the intermediate layer is equal to or substantially less than the wavelength of the surface acoustic waves of the device;

- at least one lateral dimension of the motifs is less than or equal to the wavelength of the surface acoustic waves of the device;

- the periodic motifs comprise an alternation of a first motif composed of the material of the useful layer or of the material of the carrier substrate and of a second motif composed of another material;

- the second motif is composed of silicon dioxide, of silicon nitride;

The invention also relates to a method of manufacturing a hybrid structure for a surface acoustic

wave device remarkable in that it comprises the following stages:

5 i) Providing a useful layer of piezoelectric material and a carrier substrate having a thermal expansion coefficient lower than that of the useful layer;

10 ii) Local etching according to periodic motifs of a front face of the useful layer or carrier substrate, forming a set of etched motifs and unetched motifs of a first material;

iii) Applying to the etched motifs an additional layer of a second material different from the first material, wherein the unetched periodic motifs and the additional layer form an intermediate layer;

15 iv) Assembling the useful layer and the carrier substrate such that the intermediate layer is arranged between the useful layer and the carrier substrate.

According to advantageous characteristics of the invention, taken either separately or in combination:

20 • the useful layer provided at stage i) is a piezoelectric material donor substrate;

• the method comprises a stage v) of thinning the donor substrate to the desired thickness of the useful layer for manufacture of the acoustic wave device.

25 BRIEF DESCRIPTION OF THE DRAWINGS

Further characteristics and advantages of the invention will be clear from the following detailed description, made in reference to the appended figures, in which:

- 5 - figure 1 shows a hybrid structure according to the invention;
- figure 2 shows a hybrid structure according to the invention comprising an SAW device;
- figures 3a and 3b show a hybrid structure
10 according to an embodiment in accordance with the invention;
- figures 4a to 4d show examples of periodic motifs of the intermediate layer of a hybrid structure according to the invention;
- 15 - figures 5a to 5c show sectional views of examples of motifs of the intermediate layer of a hybrid structure according to the invention.

DETAILED DESCRIPTION OF THE INVENTION

20 In the descriptive section, the same references in the futures may be used for elements of the same type. The figures are schematic representations which, for the sake of legibility, are not to scale. In particular, the thicknesses of the layers along the z axis are not to scale in relation of the lateral
25 dimensions along the x and y axes.

The invention relates to a hybrid structure 10 suitable for manufacturing a surface acoustic wave (SAW) device, comprising a useful layer 1 of

piezoelectric material, having a first face 2 and a second face 3, as illustrated in figure 1. The hybrid structure 10 also includes an intermediate layer 4 arranged under the useful layer (along the z axis shown in figure 1), in contact with the second face 2. The intermediate layer 4 is a structured layer of a thickness e , formed of at least two different materials. Structured layer implies a layer composed of periodic motifs in the plane of the layer (i.e. in the plane (x,y) in figure 1). These motifs correspond to blocks of defined lateral dimensions (i.e. the dimensions in the plane (x,y)) and of a thickness (i.e. along the z axis) less than or equal to e : they consist of at least two different materials. According to the example illustrated in figure 1, the intermediate layer 4 is composed of first motifs 6 formed of a first material and of second motifs 7 (complementary to the first motifs) formed of a second material. In the plane (x,y) , the first and second motifs 6 and 7 are of defined shape (square, rectangle, circle,) and have defined lateral dimensions.

Finally, the hybrid structure 10 comprises a carrier substrate 5 having a thermal expansion coefficient lower than that of the useful layer 1, arranged under the intermediate layer 4 (along the z axis shown in figure 1). The useful layer 1 of the hybrid structure 10 may be composed of a material selected from the following group: lithium tantalate (LiTaO_3), lithium niobate (LiNbO_3), aluminium nitride (AlN) and zinc oxide (ZnO). The carrier substrate 5 may be composed of a material selected from the following

group: silicon, III-V semiconductors, silicon carbide, glass and sapphire.

As illustrated in figure 2, the hybrid structure 10 is suitable for manufacturing surface acoustic wave (SAW) devices, comprising in particular metallic electrodes 20 on the useful layer 1, between which the acoustic signal propagates. The direction of propagation of the acoustic signal is illustrated by the arrow, in the direction of the y axis, in the example in figure 2.

According to a first embodiment of the hybrid structure 10 of the invention, the intermediate layer 4 consists of two materials: the first material (composing the first motifs 6) is that of the useful layer (piezoelectric material); the second material (composing the second motifs 7) is of the same type as the carrier substrate of the hybrid structure 10. The thickness e of the intermediate layer 4 is greater than the wavelength λ of the acoustic signal used by the SAW device; typically, e may be included between 2λ and 50λ ; this characteristic ensures that the acoustic wave that propagates in the layer of piezoelectric material sees the intermediate layer 4 and can undergo its influence. Furthermore, at least one lateral dimension (the dimension along the axis of propagation of the acoustic wave in the device) of the first and second periodic motifs is smaller than said wavelength; typically, it may be between $\lambda/2$ and $\lambda/50$.

At the scale of the acoustic wave, the intermediate layer therefore appears as a composite material, comprising the first and second materials. The lateral dimensions of the periodic motifs are selected such that the acoustic impedance of the intermediate layer 4 is substantially equal to the square root of the product of the acoustic impedances of the useful layer 1 and of the carrier substrate 5. It should be remembered that the acoustic impedance Z of a material is expressed as:

$$Z = v \cdot \rho = \sqrt{\frac{E}{3(1-2\nu)\rho}} \cdot \rho = \sqrt{\frac{E \cdot \rho}{3(1-2\nu)}}$$

where v is the velocity of the acoustic wave in the material, ρ is the density of the material, E and ν are respectively Young's modulus and the Poisson's ratio of the material.

In the case of the intermediate layer 4, one considers the volumic fractions V_1 and V_2 of each of the materials of which it is composed and its acoustic impedance can be expressed as:

$$Z_{\text{intermediate layer}} = \sqrt{\left[\left(\frac{E_1 V_1}{3(1-2\nu_1)} \right) + \left(\frac{E_2 V_2}{3(1-2\nu_2)} \right) \right] \times [(\rho_1 V_1) + (\rho_2 V_2)]}$$

where ρ_1 and ρ_2 are respectively the density of the first and the second material, E_1 and E_2 are respectively the Young's modulus of the first and second material and ν_1 and ν_2 are the Poisson's ratio of the first and second material.

The volumic fractions V_1 and V_2 are defined by the thickness e of the intermediate layer 4 and the lateral dimensions of the first and second motifs 6,7.

5 The characteristics of the intermediate layer 4 (first and second material, lateral dimensions of the periodic motifs) are thus defined such that its mean acoustic impedance is as close as possible to the square root of the product of the acoustic impedances of the useful layer 1 and of the carrier substrate 5:

$$Z_{\text{intermediate layer}} \cong \sqrt{Z_{\text{useful layer}} \times Z_{\text{substrate}}}$$

10 This configuration favours transmission of the portion of acoustic waves usually reflected at the interfaces of a hybrid structure (by adaptation of acoustic impedance) from the useful layer 1 towards the substrate 5: it thus makes it possible to drastically
15 reduce the parasitic reflections negatively impacting the frequency characteristics of the SAW device produced on the hybrid structure 10.

According to a second embodiment of the hybrid structure 10 according to the invention, the
20 intermediate layer 4 likewise consists of two materials (figure 3a), but exhibits different physical characteristics from those of the first embodiment. On the one hand, the thickness e of the intermediate layer is equal to or substantially less than the wavelength λ
25 of the acoustic signal used for the SAW device, for example included between λ and $\lambda/8$. On the other hand, at least one lateral dimension (that along the axis of

propagation of the acoustic wave in the device) of the periodic motifs is smaller than or equal to the wavelength λ of the acoustic wave; typically, it may be included between $\lambda/10$ and λ . This configuration promotes interaction between the acoustic wave and the intermediate layer 4. In particular, the portion of acoustic wave usually reflected at the interfaces of the hybrid structure will be advantageously diffused by the intermediate layer 4: this will result in substantial restriction of the reflected component of the acoustic wave causing the parasitic effects.

According to a variant of the second embodiment of the invention, the intermediate layer may consist of air or gas (at the level of the first motifs 6 forming cavities) and of a second material (at the level of the second motifs 7) (figure 3b); for example, the second motifs 7 may be formed of the same material as the carrier substrate 5. Advantageously, the materials constituting the first and second motifs respectively will be chosen so as to generate an acoustic contrast between the first and second motifs.

The lateral dimensions of the first and second motifs (and therefore the periodicity of said motifs) are defined according to the frequency of the acoustic wave characteristic of the SAW device, in addition to the thickness of the intermediate layer 4 and moreover in order to transmit or diffuse the acoustic waves normally reflected on the interfaces of the hybrid structure.

Figures 4a to 4d show variants of arrangement of the periodic motifs 6,7 of the intermediate layer 4. In the example in figure 4a, showing a top view of the intermediate layer 4, in the plane (x,y), the first motifs 6 and the second motifs 7 are strip shaped. It should be remembered that in this case, the SAW device must be produced such that propagation of the acoustic waves occurs parallel to the y axis, i.e. perpendicularly to said strips. The lateral dimensions along the y axis (width of the strips) of the first and second motifs will be selected according to the embodiments (less than or substantially equal to the wavelength of the acoustic wave). According to an alternative solution in figure 4b, the dimension of several consecutive first motifs 6 is different: for example, an alternation of first motifs 6 with strips 61, 62, 63 of different widths along the y axis is observed. A similar alternation can also be performed on the second motifs 7 with strips 71, 72, 73 of different widths. This alternation is periodically repeated over the entire surface of the intermediate layer 4. A configuration of this kind is particularly favourable in the second embodiment of the invention in diffusing the acoustic waves over a wider frequency range.

According to another alternative solution illustrated in figure 4c, the first motifs are pads, which are square-shaped for example, the dimensions of which along the x axis and y axis are defined according to the criteria of the first or second embodiments of the invention. The second motifs are the motifs

complementary to the first motifs in the plane (x, y) . Such an arrangement of motifs makes the hybrid structure 10 independent from the orientation of the devices and from the direction of propagation of the acoustic waves. According to another alternative solution in figure 4d, the first motifs are squares of different dimensions, repeated periodically. A configuration of this kind is interesting in the second embodiment of the invention in diffusing the acoustic waves over a wider frequency range.

Figures 5a to 5c show sectional views of hybrid structures according to the invention. The periodic motifs 6,7 of the intermediate layer 4 may have different shapes along the z axis. According to one alternative version, they form slots (figure 5a and 5b); the first motifs 6 have dimensions along z less than or equal to the thickness of the intermediate layer 4. According to another alternative solution (figure 5c), they form V-shaped motifs, capable of optimising diffusion of the spurious waves by orienting the reflection planes between the motifs in the intermediate layer 4.

The examples mentioned are of course not exhaustive and the motifs may be of various shapes, in the plane (x,y) or in a perpendicular plane without going beyond the ambit of the invention.

According to an alternative solution applicable to the first or second embodiment of the hybrid

structure 10, the intermediate layer may be formed of three or more different materials.

5 The invention also relates to a method of manufacturing a hybrid structure 10 for a surface acoustic wave device. The method comprises a first stage of providing a useful layer 1 of piezoelectric material. According to an advantageous mode of implementation, the useful layer adopts the form of a substrate of piezoelectric material, of a thickness and
10 diameter standard in the micro-electronics industry (for example, a diameter of 150 mm and a thickness of 675 microns).

The first stage also comprises providing a carrier substrate 5 having a thermal expansion
15 coefficient lower than that of the donor substrate (i.e. also that of the useful layer 1).

The manufacturing method according to the invention comprises a second stage involving local etching of a front face of the donor substrate
20 according to periodic motifs, thereby forming a set of etched motifs and unetched motifs. With reference to the hybrid structure described above, the etched motifs may be either the first or the second motifs (the same applies to the unetched motifs). This etching stage can
25 for example be carried out by dry or wet chemical attack, laser etching or another technique suitable for local etching of micrometric motifs. Prior to the etching stage, a photolithography stage can be performed to define the areas to be etched.

Alternatively, the second etching stage can be performed on a front face of the carrier substrate instead of on the donor substrate.

5 The manufacturing process comprises a third stage of applying, to the etched motifs, an additional layer of a second material different from the first material forming the non-etched motifs. This additional layer may be formed for example by chemical vapour deposition, chemical liquid deposition or by epitaxy,
10 etc.

The unetched periodic motifs and the additional layer form the intermediate layer 4 of the hybrid structure 10 according to the invention. Advantageously, the depth of the etching (defining the
15 height, along the z axis, of the unetched motifs) defines the thickness e of the intermediate layer 4. The additional layer can advantageously undergo a planarisation or surface smoothing treatment prior to the next assembly stage.

20 The method comprises a fourth stage of assembly of the donor substrate and the carrier substrate 5, so that the intermediate layer 4 is arranged between these two substrates. Advantageously, the assembly stage is carried out by direct bonding, by molecular adhesion of
25 the two surfaces placed in contact (i.e. without the surface of the intermediate layer 4 and the surface of the substrate having any intermediate layer). The principle of molecular adhesion, well known in the state of the art, will not be described in further

detail. Alternatively, assembly can be carried out by adding a layer of adhesive material, or by any other bonding technique suitable for the intended application.

5 The manufacturing method according to the invention furthermore comprises a fifth stage of thinning the donor substrate to the desired thickness of the useful layer 1 for manufacture of the acoustic wave device. This stage may for example involve
10 mechanical grinding, followed by dry or chemical mechanical polishing, ensuring a good surface finish for the useful layer 1. Various different cleaning sequences may of course be implemented during or after the thinning stage to guarantee the quality and
15 cleanliness of the final hybrid structure 10.

Example 1:

 In an exemplary implementation of the invention, a donor substrate made of lithium niobate (LiNbO_3) and a carrier substrate made of silicon 5, both having a
20 diameter of 150 mm and a thickness of 675 microns are provided. The resistivity of the carrier substrate will be selected for example $> 1000 \text{ ohms.cm}$. The LiNbO_3 donor substrate undergoes a photolithography stage to define the motifs: the first motifs 6 are defined as the areas
25 not to be etched; the second motifs 7 are defined as the motifs to be etched. The first motifs correspond to 0.3-micron-square tabs, spaced 0.2 microns apart. The second motifs correspond to a grid between the tabs, the strip width of which is 0.2 microns, i.e. the area

complementary to said tabs on the surface of the donor substrate. The stage of etching the surface of the donor substrate is performed by dry etching, over a depth of 5 microns. After removing the photolithography mask on the surface of the donor substrate and cleaning the latter (by an RCA sequence for example, conventionally used in the micro-electronics industry), an additional layer of polycrystalline silicon is applied by CVD (chemical vapour deposition) for example.

In order to fill in the etched areas (second motifs), a thickness of between 6 and 12 microns, advantageously 8 microns, can be applied. A stage of planarisation by chemical mechanical polishing is subsequently effected to eliminate any residual topologies and roughnesses following the application of p-Si.

The intermediate layer 4 consists of the first motifs 6 made of piezoelectric material and the additional layer (p-Si) filling the second motifs 7. In a first alternative solution, the thickness of the intermediate layer 4 corresponds to the etching depth, i.e. 5 microns in this example; in this case, the planarisation stage will have allowed removal of the polycrystalline silicon from the surface of the donor substrate until flush with the first motifs (configuration illustrated in figure 5b). In a second alternative solution, the thickness e of the intermediate layer 4 is greater than the etching depth, since a thickness of the additional layer remains on

the first motifs (configuration illustrated in figure 5a, wherein in the additional layer is between and under the first motifs 6 in the final hybrid structure 10 represented in said figure). By way of example, the additional layer on top of the first motifs may be 1 micron in thickness: the intermediate layer will thus be 6 microns in thickness.

Once the surface of the donor substrate has been prepared, the stage of assembly with the carrier substrate 5 is performed. A sequence of cleaning the two substrates may be effected prior to assembly, particularly in the case of direct bonding by molecular adhesion, which is particularly sensitive to the presence of contamination or particles on the surfaces to be assembled. In order to increase the adhesion forces between the substrates, their surfaces may undergo oxygen or nitrogen plasma treatment before being placed in contact.

After bonding, low-temperature reinforcement annealing is carried out, usually within the range of 80-120°C, given the major difference in thermal expansion between the materials of the assembled substrates.

A stage of mechanical thinning followed by a stage of chemical mechanical polishing of the rear face of the donor substrate is effected to obtain the useful layer of the hybrid structure, with a thickness of 20 microns.

The hybrid structure obtained is therefore composed of a useful layer of LiNbO_3 20 microns in thickness, an intermediate layer of a thickness of between 5 and 6 microns (according to the alternative solutions mentioned above) and composed of two materials: first motifs made of LiNbO_3 and second motifs made of polysilicon. The size of the first motifs in the plan (x,y) is 0.3 microns and their distance apart is 0.2 microns. The mean acoustic impedance of this layer is therefore approximately $1.5\text{e}6 \text{ g/cm}^2/\text{sec}$, i.e. a value very close to the square root of the product of the impedances of the LiNbO_3 and silicon.

This hybrid structure is intended for manufacturing a surface acoustic wave device, the wavelength λ of which is on the order of 2 microns. Given the limited thickness of the useful layer, a portion of the acoustic waves penetrates into the layer and propagates to reach the intermediate layer. These waves are usually reflected on the interfaces (LiNbO_3/Si for example) and generate spurious waves impairing the performance of the device.

The configuration of the intermediate layer 4 of the hybrid structure 10 according to the invention promotes transmission towards the silicon carrier substrate 5 of the acoustic waves penetrating into the depth of the useful layer 1. The mean acoustic impedance of the intermediate layer 4 is properly suited to the surrounding materials (LiNbO_3 and Si). The thickness e of the intermediate layer 4 is greater than the wavelength of the acoustic wave of the device; the

size and distance between the first motifs are smaller than the wavelength.

Furthermore, the hybrid 10 structure described here has a significant advantage regarding the RF performance of the device. Indeed, the additional layer of polysilicon forms a trapping layer for the charges generated in the silicon carrier substrate 5 when the latter is subjected to high frequency signals. These charges are known to cause a drop in the resistivity of the carrier substrate 5, which negatively affects the linearity and insertion loss performances of the RF device. The additional layer of p-Si therefore plays a supplementary role as a trapping layer and neutralises the charges generated in the carrier substrate 5.

Example 2:

In another exemplary implementation of the invention, a donor substrate made of lithium tantalate (LiTaO_3) and a carrier substrate made of silicon, both having a diameter of 150 mm and a thickness of 675 microns are provided. The resistivity of the carrier substrate will be selected for example $> 1000 \text{ ohms.cm}$. The LiTaO_3 donor substrate undergoes a photolithography stage to define the motifs (in the plane (x,y)): the first motifs 6 are defined as the areas not to be etched; the second motifs 7 are defined as the motifs to be etched. The first motifs 6 correspond to strips 1.25 microns in width, spaced 1.25 microns apart. The second motifs 7 correspond to strips complementary to the strips of the first motifs

6, on the surface of the donor substrate. The stage of etching the surface of the donor substrate is performed by dry etching, over a depth of approximately 1.5 microns. After removing the photolithography mask on the surface of the donor substrate and cleaning the latter, an additional layer of silicon oxide is applied by CVD (chemical vapour deposition) for example. In order to fill in the etched areas (second motifs), a thickness of between 2 and 6 microns, advantageously 4 microns, will be applied. A stage of planarisation by chemical mechanical polishing of the additional layer is subsequently effected to eliminate any residual topologies and roughnesses following the application of oxide.

The intermediate layer 4 consists of the first motifs 6 made of piezoelectric material (LiTaO_3) and the additional layer (SiO_2) filling the second motifs 7. In a first alternative solution, the thickness of the intermediate layer 4 corresponds to the etching depth, i.e. 1.5 microns in this example; in this case, the planarisation stage will have allowed removal of the silicon oxide from the surface of the donor substrate until flush with the first motifs 6. In a second alternative solution, the thickness of the intermediate layer 4 is greater than the etching depth, since a thickness of the additional layer remains on the first motifs 6. For example, the additional layer on top of the first motifs 6 may be 0.5 microns in thickness: the intermediate layer 4 will thus be 2 microns in thickness.

Once the surface of the donor substrate has been prepared, the stage of assembly with the carrier substrate is performed. A sequence of cleaning the two substrates may be effected prior to assembly, particularly in the case of direct bonding by molecular
5 adhesion, which is particularly sensitive to the presence of contamination or particles on the surfaces to be assembled. In order to increase the adhesion forces between the substrates, their surfaces may
10 undergo oxygen or nitrogen plasma treatment before being placed in contact.

After bonding, low-temperature reinforcement annealing is carried out, usually within the range of 80-120°C, given the major difference in thermal
15 expansion between the materials of the assembled substrates.

A stage of mechanical thinning followed by a stage of chemical mechanical polishing of the rear face of the donor substrate is effected to obtain the useful
20 layer of the hybrid structure, with a thickness of 30 microns.

The hybrid structure obtained is therefore composed of a useful layer of LiTaO_3 30 microns in thickness, an intermediate layer of a thickness of
25 between 1.5 and 2 microns (according to the alternative solutions mentioned above) and composed of two materials: first motifs made of LiTaO_3 and second motifs made of silicon oxide. The size of the first motifs in

the y axis is 1.25 microns and their distance apart is 1.25 microns.

This hybrid structure 10 is intended for manufacturing a surface acoustic wave device, the frequency of which is within the range of 700-900 MHz, i.e. a wavelength on the order of 5 microns. Propagation of the acoustic waves will occur along the y axis. Given the limited thickness of the useful layer, a portion of the acoustic waves penetrates into the useful layer 1 and propagates to reach the intermediate layer 4. These waves are usually reflected on the interfaces (LiTaO_3/Si for example) and generate spurious waves impairing the performance of the device.

The configuration of the intermediate layer 4 of the hybrid structure 10 according to the invention promotes diffusion on the intermediate layer 4 of the acoustic waves penetrating into the useful layer 1 and therefore limits their reflection. The thickness e of the intermediate layer 4 is substantially less than the wavelength of the acoustic wave of the device; the size and distance between the first motifs are smaller than the wavelength.

Example 3:

In another exemplary implementation of the invention, a donor substrate made of lithium tantalate (LiTaO_3) and a carrier substrate made of silicon, both having a diameter of 150 mm and a thickness of 625 microns are provided. The resistivity of the carrier substrate will be selected for example >

1000 ohms.cm. The carrier substrate undergoes a photolithography stage to define the motifs: the first motifs 6 are defined as the areas not to be etched; the second motifs 7 are defined as the motifs to be etched.

5 The first motifs 6 correspond to strips 1.25 microns in width, spaced 1.25 microns apart. The second motifs correspond to strips complementary to the strips of the first motifs, on the surface of the carrier substrate.

10 The stage of etching the surface of the carrier substrate is performed by dry etching, over a depth of 1 micron. After removing the photolithography mask on the surface, the carrier substrate is cleaned with a view to carrying out the stage of assembly with the donor substrate. No additional layer is applied in this

15 third example. The first material (constituting the first motifs) is silicon and the second material is air or a gas depending on the atmosphere introduced into the bonding chamber during the assembly stage.

After bonding, low-temperature reinforcement

20 annealing is carried out, usually within the range of 80-120°C, given the major difference in thermal expansion between the materials of the assembled substrates.

A stage of mechanical thinning followed by a

25 stage of chemical mechanical polishing of the rear face of the donor substrate is effected to obtain the useful layer of the hybrid structure, with a thickness of 20 microns.

The hybrid structure obtained is therefore composed of a useful layer of LiTaO_3 20 microns in thickness, an intermediate layer of a thickness of 1 micron and composed of two materials: first motifs
5 made of silicon and second motifs filled with air or gas. The size of the first motifs in the y axis is 1.25 microns and their distance apart is 1.25 microns.

This hybrid structure is intended for manufacturing a surface acoustic wave device, the
10 frequency of which is 700-900 MHz, i.e. a wavelength on the order of 5 microns. Given the limited thickness of the useful layer, a portion of the acoustic waves penetrates into the layer and propagates to reach the intermediate layer 4. These waves are usually reflected
15 on the interfaces (LiTaO_3/Si for example) and generate spurious waves impairing the performance of the device.

The configuration of the intermediate layer 4 of the hybrid structure 10 according to the invention promotes diffusion on the intermediate layer 4 of the
20 acoustic waves penetrating into the useful layer 1 and therefore limits their reflection. The thickness e of the intermediate layer 4 is substantially less than the wavelength of the acoustic wave of the device; the size and distance between the first motifs are smaller than
25 the wavelength.

Of course, the invention is not limited to the described embodiments and examples and variant embodiments can be provided without leaving the scope of the invention as defined in the claims.

The hybrid structure 10 according to the invention can in particular be adapted to the manufacture of surface acoustic wave devices, the frequency of which is within the range of 700 MHz - 3 GHz.

CLAIMS

1. Hybrid structure (10) for a surface acoustic wave device comprising a useful layer (1) of piezoelectric material joined to a carrier substrate (5) having a thermal expansion coefficient lower than that of the useful layer (1), characterised in that it comprises an intermediate layer (4) located between the useful layer (1) and the carrier substrate (5), the intermediate layer (4) being a structured layer formed of at least two different materials having a plurality of periodic motifs (6,7) in the plane of said intermediate layer (4).

2 Hybrid structure (10) for a surface acoustic wave device according to the preceding claim, wherein the periodicity of the motifs (6,7) is selected according to the frequency of the surface acoustic waves of the device.

3. Hybrid structure (10) for a surface acoustic wave device according to any of the preceding claims, wherein the carrier substrate (5) comprises a material selected from among silicon, glass, silica, sapphire, alumina and aluminium nitride.

4. Hybrid structure (10) for a surface acoustic wave device according to any of the preceding claims, wherein the useful layer (1) comprises a piezoelectric material selected from among lithium tantalate (LiTaO_3), lithium niobate (LiNbO_3), quartz and zinc oxide (ZnO).

5. Hybrid structure (10) for a surface acoustic wave device according to any of the preceding claims, wherein the mean acoustic impedance of the intermediate layer (4) is equal to the square root of the product of the acoustic impedances of the useful layer (1) and of the carrier substrate (5).

6. Hybrid structure (10) for a surface acoustic wave device according to any of the preceding claims, wherein the thickness of the intermediate layer (4) is greater than the wavelength of the surface acoustic waves of the device.

7. Hybrid structure (10) for a surface acoustic wave device according to any of the preceding claim, wherein at least one lateral dimension of the motifs (6,7) is smaller than the wavelength of the surface acoustic waves of the device.

8. Hybrid structure (10) for a surface acoustic wave device according to any of the preceding claims, wherein the periodic motifs (6,7) comprise an alternation of a first motif (6) composed of the material of the useful layer (1) and of a second motif (7) composed of a material of the same type as that of the carrier substrate (5).

9. Hybrid structure (10) for a surface acoustic wave device according to the preceding claim, wherein the second motif (7) is composed of polycrystalline silicon and wherein the carrier substrate (5) is made of silicon.

10. Hybrid structure (10) for a surface acoustic wave device according to any of claims 1 to 4, wherein the thickness of the intermediate layer (4) is equal to or smaller than the wavelength of the surface acoustic waves of the device.

11. Hybrid structure (10) for a surface acoustic wave device according to the preceding claim, wherein at least one lateral dimension of the motifs (6,7) is smaller than or equal to the wavelength of the surface acoustic waves of the device.

12. Hybrid structure (10) for a surface acoustic wave device according to any of both preceding claims, wherein the periodic motifs (6,7) comprise an alternation of a first motif (6) composed of the material of the useful layer (1) and of a second motif (7) composed of another material.

13. Hybrid structure (10) for a surface acoustic wave device according to the preceding claim, wherein the second motif (7) is composed of silicon dioxide or silicon nitride.

14. Method of manufacturing a hybrid structure (10) for a surface acoustic wave device, characterised in that it comprises the following stages:

i) Providing a useful layer (1) of piezoelectric material and a carrier substrate (5) having a thermal expansion coefficient lower than that of the useful layer (1);

ii) Local etching according to periodic motifs of a front face of the useful layer (1) or carrier substrate (5), forming a set of etched motifs and unetched motifs of a first material;

5 iii) Applying to the etched motifs an additional layer of a second material different from the first material, wherein the unetched periodic motifs and the additional layer form an intermediate layer (4);

10 iv) Assembling the useful layer (1) and the carrier substrate (5) such that the intermediate layer (4) is arranged between the useful layer (1) and the carrier substrate (5).

15 15. Method of manufacturing a hybrid structure (10) for a surface acoustic wave device according to the preceding claim, wherein the useful layer (1) provided at stage i) is a piezoelectric material donor substrate.

20 16. Method of manufacturing a hybrid structure (10) for a surface acoustic wave device according to the preceding claim, comprising a stage v) of thinning the donor substrate to the desired thickness of the useful layer (1) for manufacture of the acoustic wave device.